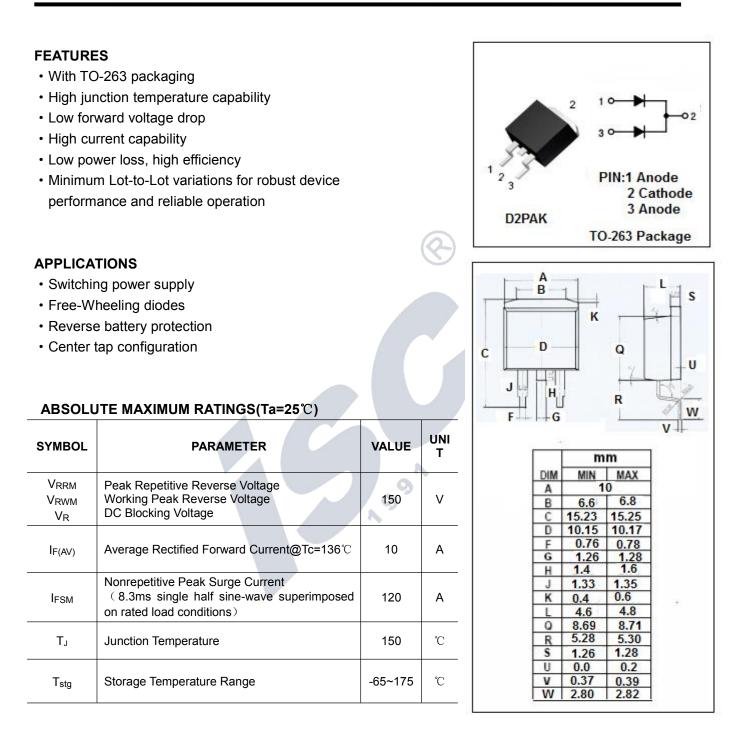


INCHANGE SEMICONDUCTOR

Schottky Barrier Rectifier

MBRS10150CT



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MBRS10150CT

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	2.0	°C /W

ELECTRICAL CHARACTERISTICS (Pulse Test: Pulse Width=300 µ s,Duty Cycle≤1%)

SYMBOL	PARAMETER	CONDITIONS	МАХ	UNIT
VF	Maximum Instantaneous Forward Voltage	I _F = 5A ; Tc= 25℃	0.88	V
		I _F = 5A ; Tc= 125℃	0.78	
IR	Maximum Instantaneous Reverse Current	V _R = V _{RWM:} Tc= 25°С	0.1	mA
		Vr= V _{RWM:} Tc= 125°С	5	



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